NSN 5961-00-188-3974

Photo Semiconductor Device - Page 1 of 1

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Inclosure Material:

Metal and glass

Overall Length:

Between 0.180 inches and 0.210 inches

Terminal Length:

1.500 inches

Overall Diameter:

Between 0.209 inches and 0.230 inches

Function For Which Designed:

Detector

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Terminal

Terminal Circle Diameter:

0.100 inches

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

50.0 collector to emitter voltage/static/base open and 7.0 emitter to collector voltage, dc and 80.0 collector to base voltage/static/emitter open

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: npn

Terminal Type And Quantity:

3 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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